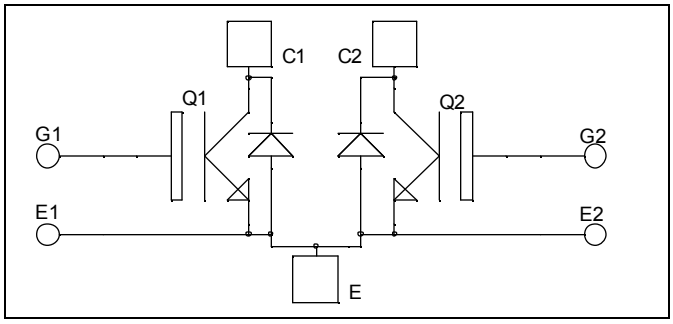
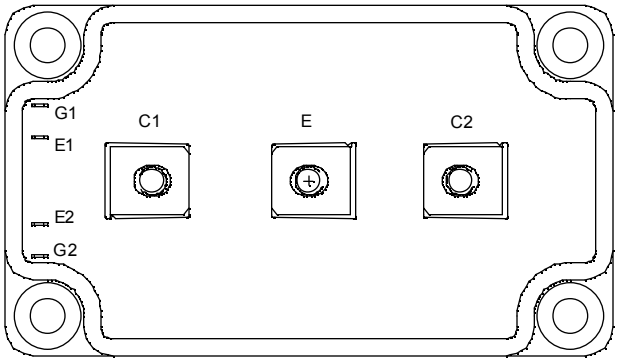
APTGT150DU170

Dual common source Trench + Field Stop IGBT® Power Module

V_{CES} = 1700V
I_C = 150A @ Tc = 80°C





Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT® Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		1700	V
I_C	Continuous Collector Current	T_C = 25°C	250	A
		T_C = 80°C	150	
I_{CM}	Pulsed Collector Current	T_C = 25°C	300	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	890	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 125°C	300A @ 1600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 1700V				350	µA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	V_{GE} = 15V, I_C = 150A	T_j = 25°C		2.0	2.4	V
			T_j = 125°C		2.4		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE}, I_C = 3mA		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				600	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz		13.5		nF
C_{oes}	Output Capacitance			0.55		
C_{res}	Reverse Transfer Capacitance			0.44		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = 15V V_{Bus} = 900V I_C = 150A R_G = 4.7Ω		370		ns
T_r	Rise Time			40		
$T_{d(off)}$	Turn-off Delay Time			650		
T_f	Fall Time			180		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = 15V V_{Bus} = 900V I_C = 150A R_G = 4.7Ω		400		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			800		
T_f	Fall Time			300		
E_{on}	Turn-on Switching Energy			48		mJ
E_{off}	Turn-off Switching Energy			47		

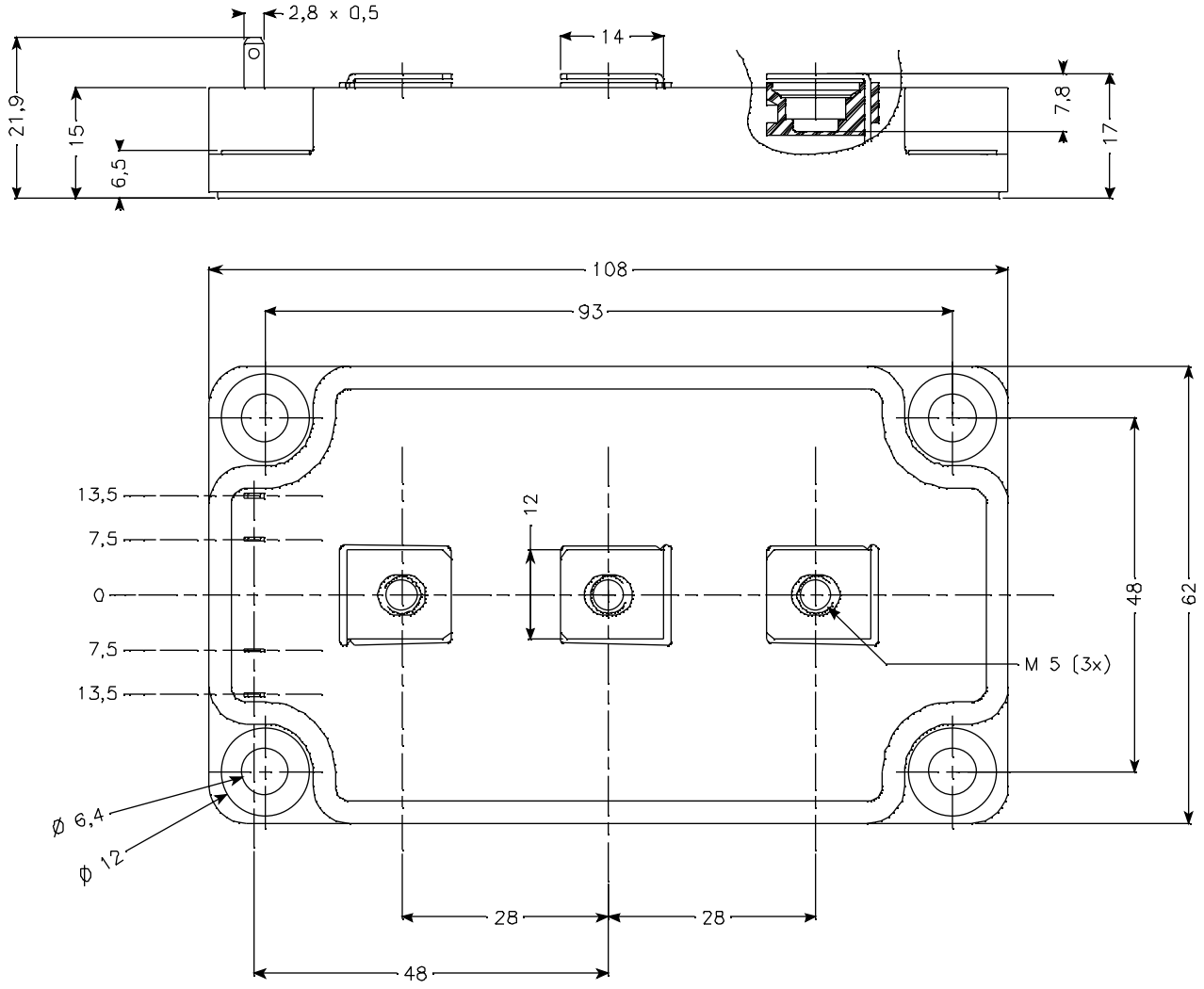
Diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1700			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1700V	T_j = 25°C			350	µA
			T_j = 125°C			600	
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle	Tc = 80°C		150		A
V_F	Diode Forward Voltage	I_F = 150A	T_j = 25°C		1.8	2.2	V
			T_j = 125°C		1.9		
t_{rr}	Reverse Recovery Time	I_F = 150A V_R = 900V di/dt =1600A/µs	T_j = 25°C		385		ns
			T_j = 125°C		490		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		40		µC
			T_j = 125°C		64		

Thermal and package characteristics

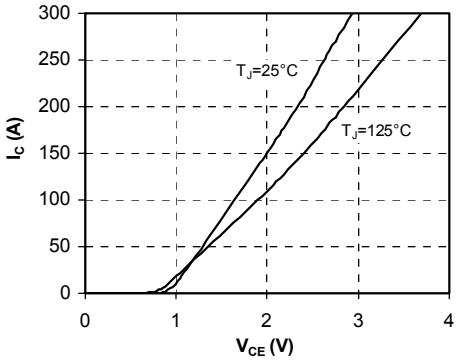
Symbol	*Characteristic*			*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case		IGBT			0.14	°C/W
			Diode			0.26	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			3400			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	
Wt	Package Weight					280	g

Package outline (dimensions in mm)

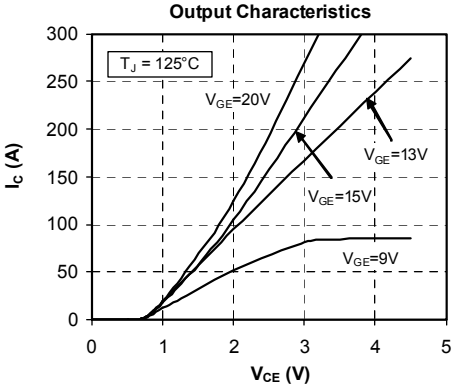


Typical Performance Curve

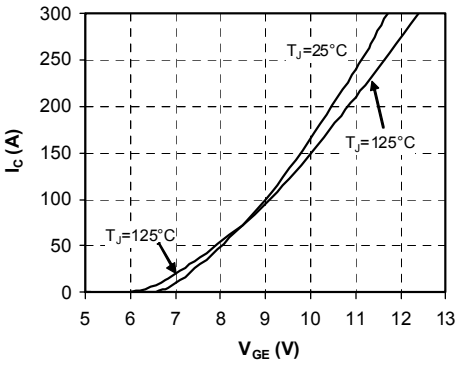
Output Characteristics (V_{GE}=15V)



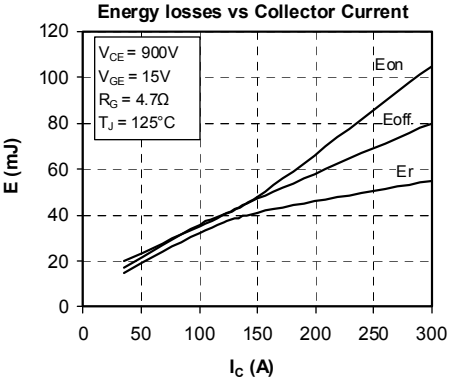
Output Characteristics



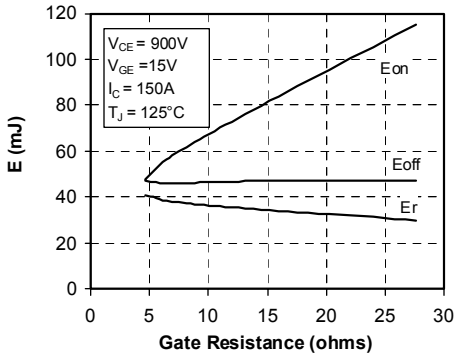
Transfert Characteristics



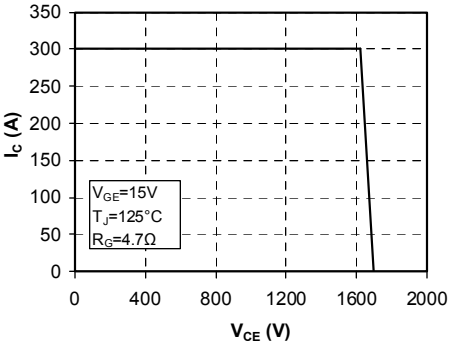
Energy losses vs Collector Current



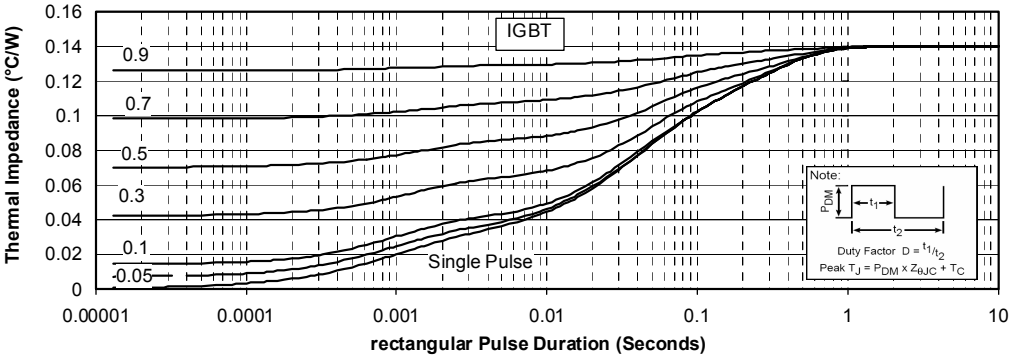
Switching Energy Losses vs Gate Resistance



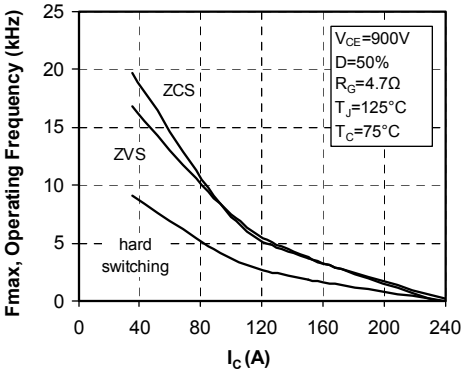
Reverse Bias Safe Operating Area



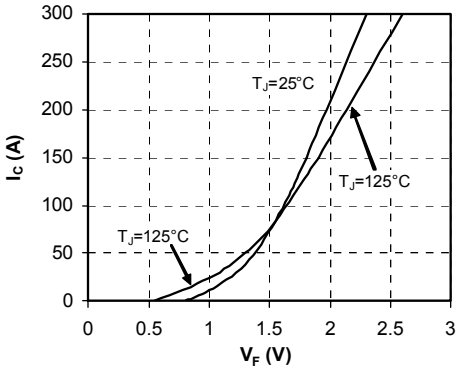
maximum Effective Transient Thermal Impedance, Junction to Pulse Duration



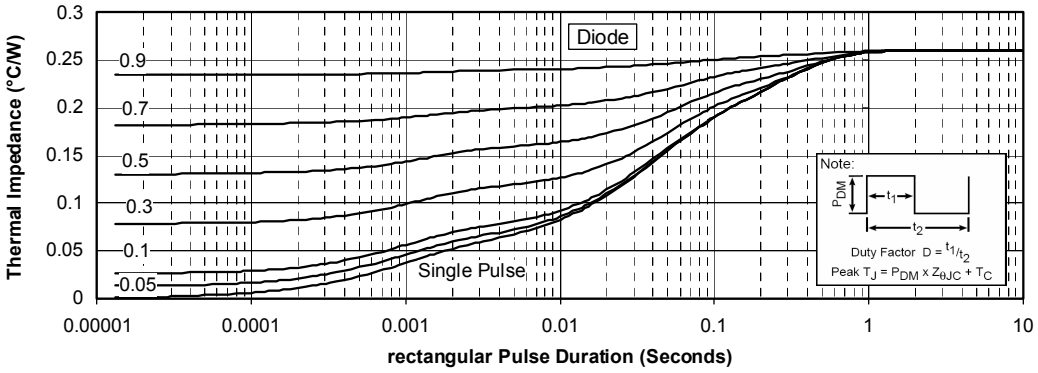
Operating Frequency vs Collector Current



Forward Characteristic of diode



maximum Effective Transient Thermal Impedance, Junction to Pulse Duration



APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.